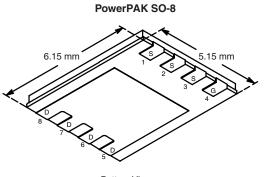


**Vishay Siliconix** 

# N-Channel Reduced Q<sub>g</sub>, Fast Switching MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω <b>)</b>	I <sub>D</sub> (A)		
30	0.008 at V <sub>GS</sub> = 10 V	18		
	0.011 at V <sub>GS</sub> = 4.5 V	15		



#### Bottom View

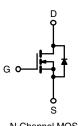
#### Ordering Information: Si7860DP-T1 Si7860DP-T1-E3 (Lead (Pb)-free) Si7860DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

### **FEATURES**

- Halogen-free According to IEC 61249-2-21
  Available
- TrenchFET<sup>®</sup> Power MOSFET
- PWM Optimized for High Efficiency
- New Low Thermal Resistance
- PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- 100 % R<sub>g</sub> Tested

#### **APPLICATIONS**

- Buck Converter
  High Side or Low Side
- Synchronous Rectifier
- Secondary Rectifier



N-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		v	
Continuous Drain Current (T - 150 °C)a	T <sub>A</sub> = 25 °C		18	11		
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T <sub>A</sub> = 70 °C	I <sub>D</sub>	15	8		
Pulsed Drain Current		I <sub>DM</sub>	± 50		А	
Continuous Source Current (Diode Continuous) <sup>a</sup>		۱ <sub>S</sub>	4.1	1.5		
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	30 45			
Single Pulse Avalanche Energy	L = 0.1 mm	E <sub>AS</sub>			mJ	
Mariana Dississioni a	T <sub>A</sub> = 25 °C	P <sub>D</sub>	5	1.8	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		3.2	1.1	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) <sup>b,c</sup>			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lumation to Ambient (MOOFET)	t ≤ 10 s	R <sub>thJA</sub>	20	25	
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	Steady State		56	70	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.8	2.3	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishav.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



HALOGEN

FREE

# Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u> </u>					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	
		$V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C			5	μA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5$ V, $V_{GS}$ = 10 V	40			Α
	R <sub>DS(on)</sub>	$\frac{V_{GS} = 10 \text{ V}, \text{ I}_{D} = 18 \text{ A}}{V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}}$		0.0066	0.008	Ω
Drain-Source On-State Resistance <sup>a</sup>				0.0090	0.011	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 18 \text{ A}$		60		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 3 \text{ A}, V_{GS} = 0 \text{ V}$		0.70	1.1	V
Dynamic <sup>b</sup>	<u> </u>					
Total Gate Charge	Qg			13	18	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 18 \text{ A}$		5		
Gate-Drain Charge	Q <sub>gd</sub>			4.0		
Gate Resistance	Rg		0.5	1.7	3.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			18	27	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		12	18	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$t_{d(off)}$ I <sub>D</sub> $\cong$ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 $\Omega$		46	70	
Fall Time	t <sub>f</sub>			19	30	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 3 A, dI/dt = 100 A/μs		40	70	

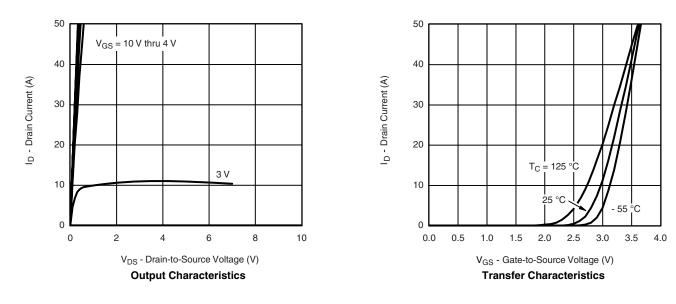
Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

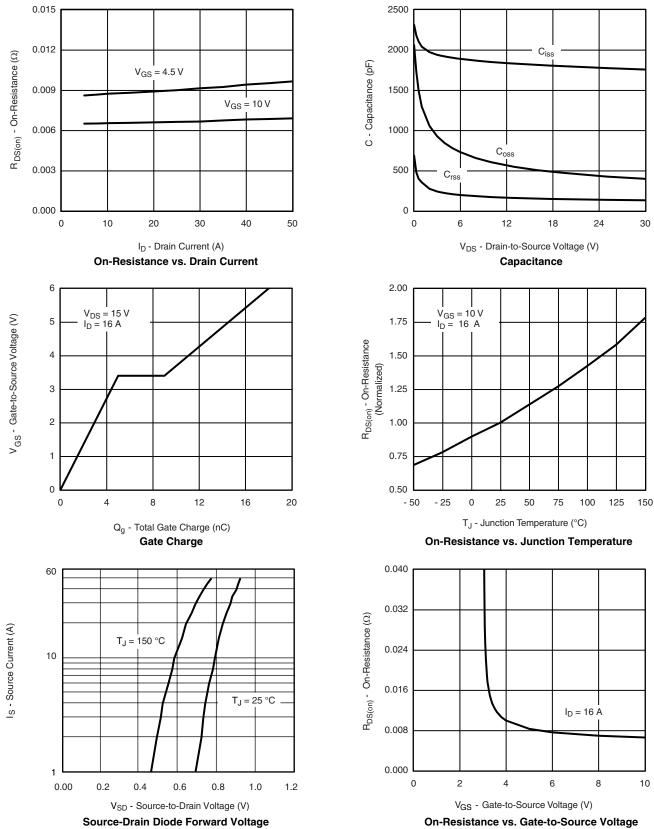


Si7860DP

Vishay Siliconix



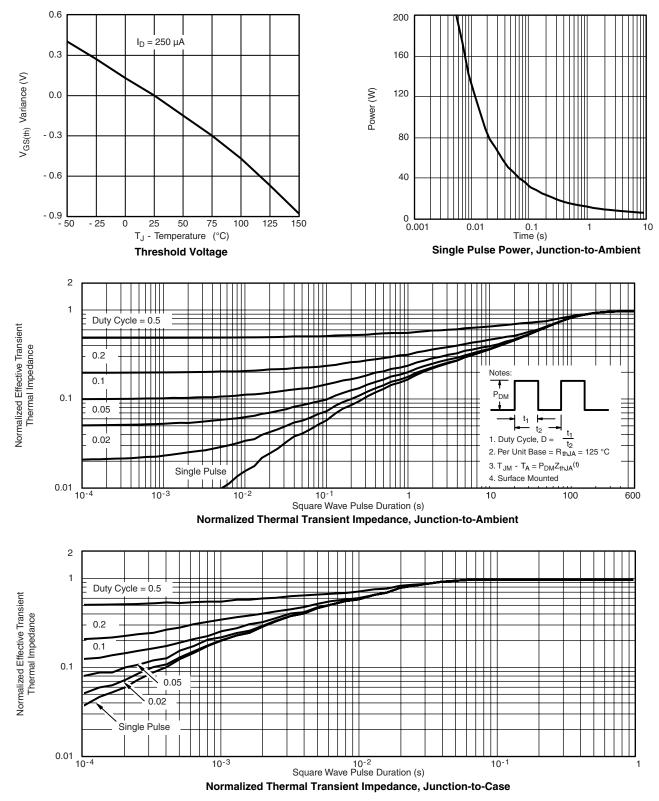
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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?71854">www.vishay.com/ppg?71854</a>.



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